

# 2SC4111

Silicon NPN triple diffusion planar type

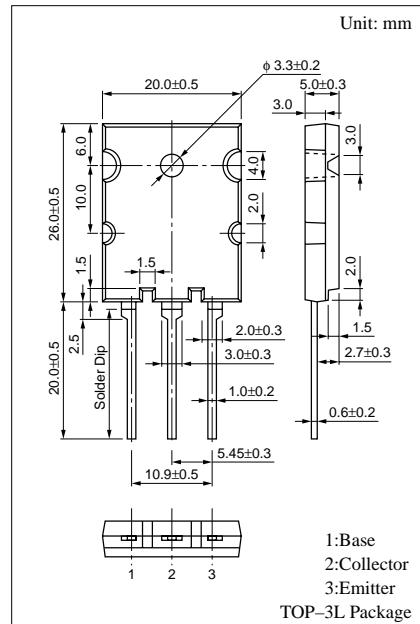
For horizontal deflection output

## ■ Features

- High-speed switching
- High collector to base voltage  $V_{CBO}$
- Wide area of safe operation (ASO)
- Satisfactory linearity of forward current transfer ratio  $h_{FE}$

## ■ Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	1500	V
Collector to emitter voltage	$V_{CES}$	1500	V
	$V_{CEO}$	700	V
Emitter to base voltage	$V_{EBO}$	7	V
Peak collector current	$I_{CP}$	22	A
Collector current	$I_C$	10	A
Base current	$I_B$	3.5	A
Collector power dissipation	$P_C$	150	W
		3.5	
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



## ■ Electrical Characteristics ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 750\text{V}, I_E = 0$			10	$\mu\text{A}$
		$V_{CB} = 1500\text{V}, I_E = 0$			1	mA
Emitter to base voltage	$V_{EBO}$	$I_C = 1\text{mA}, I_B = 0$	7			V
Forward current transfer ratio	$h_{FE1}$	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	5			
	$h_{FE2}$	$V_{CE} = 5\text{V}, I_C = 7\text{A}$	3		8	
Collector to emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = 7\text{A}, I_B = 2.5\text{A}$			5	V
Base to emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C = 7\text{A}, I_B = 2.5\text{A}$			1.5	V
Transition frequency	$f_T$	$V_{CE} = 10\text{V}, I_C = 1\text{A}, f = 0.5\text{MHz}$	2			MHz
Storage time	$t_{stg}$	$I_C = 6\text{A}, L_{\text{leak}} = 5\mu\text{H}, I_{B1} = 1.7\text{A}, I_{B2} = -1.7\text{A}$			12	$\mu\text{s}$
Fall time	$t_f$				0.6	$\mu\text{s}$

